

HALOGEN

FREE

Precision Monolithic Quad SPST CMOS Analog Switches

DESCRIPTION

The DG1411, DG1412, DG1413 are \pm 15 V precision monolithic quad single-pole single-throw (SPST) CMOS analog switches. Built on a new CMOS process, the Vishay Siliconix DG1411, DG1412, and DG1413 offer low on-resistance of 1.5 Ω . The low and flat resistance over the full signal range ensures excellent linearity and low signal distortion. The new CMOS platform provides low power dissipation, minimized parasitic capacitance, and low charge injection.

The devices operate from either a single 4.5 V to 24 V power supply, or from dual \pm 4.5 V to \pm 15 V power supplies. The analog switches don't require a V_L logic supply, while all digital inputs have 0.8 V and 2 V logic thresholds to ensure low-voltage TTL / CMOS compatibility.

The DG1411, DG1412, and DG1413 are bi-directional and support analog signals up to the supply voltage when on, and block them when off. The devices each feature four independently selectable SPST switches. The DG1411 is normally closed, while the DG1412 is normally open. The DG1413 has two normally open and two normally closed switches with guaranteed break-before-make operation.

Combined with fast 100 ns switching times, the improved performance of the DG1411, DG1412, and DG1413 make the devices ideal for signal switching and relay replacement in data acquisition, industrial control and automation, communication, and A/V systems, in addition to medical instrumentation and automated test equipment.

The switches are available in RoHS-compliant, halogen-free TSSOP16 and QFN16 4 mm by 4 mm packages.

FEATURES

- 35 V supply max. rating
- On-resistance: 1.5 Ω
- On-resistance flatness: 0.3 Ω
- Channel to channel ON-resistance match: 0.1 Ω
- · Supports single and dual supply operation
- Fully specified at ± 15 V, ± 5 V, and +12 V
- Integrated V_I supply
- 3 V logic compatible
- \bullet Low parasitic capacitance: $C_{S(OFF)}\!\!:$ 11 pF, $C_{D(ON)}\!\!:$ 87 pF
- · Rail to rail signal handling
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

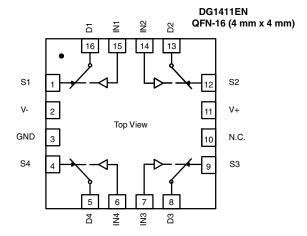
BENEFITS

- · Low insertion loss
- Low distortion
- · Break-before-make switching
- Low charge injection over the full signal range

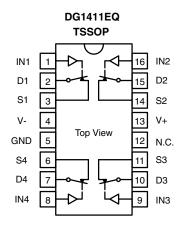
APPLICATIONS

- Medical and Healthcare equipment
- Data acquisition system
- · Industrial control and automation
- Test and measurement equipment
- · Communication systems
- Battery powered systems
- · Sample and hold circuits
- Audio and video signal switching
- Relay replacement

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG1411



TRUTH TABLE - DG1411					
LOGIC	SWITCH				
0	On				
1	Off				



Notes

- QFN EXPOSED PAD TIED TO V-
- N.C. = NO CONNECT
- Switches Shown for Logic "0" Input

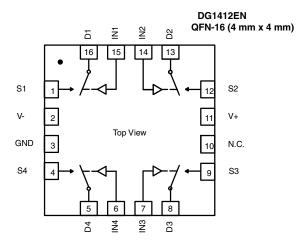
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FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG1412



	TSSOP						
IN1		IN2					
D1	2 4 6 15	D2					
S1	3 14	S2					
V-	4 Top View 13	V+					
GND	5 12	N.C.					
S4	6 11	S3					
D4	7-0-10	D3					
IN4		IN3					

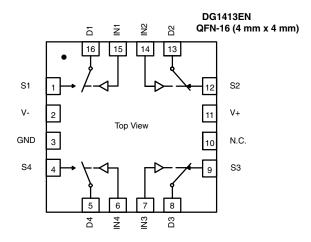
DG1412EQ

TRUTH TABLE - DG1412					
LOGIC	SWITCH				
0	Off				
1	On				

Notes

- . QFN EXPOSED PAD TIED TO V-
- N.C. = NO CONNECT
- Switches Shown for Logic "0" Input

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG1413



DG1413EQ								
	TSSOP							
IN1		7	$\mathcal{I}_{\mathcal{A}}$]	IN2			
IIN I	\Box	7	7	16	IINZ			
D1	2	~^┪	_~_	15	D2			
S1	3			14	S2			
V-	4			13	V+			
GND	5	Тор	View	12	N.C.			
S4	6			11	S3			
D4	7	~ _♥	4~	10	D3			
IN4	8	ФТ,	\vdash	9	IN3			
				_				

DC1/112EO

TRUTH TABLE - DG1413							
LOGIC	SWITCHES 1, 4	SWITCHES 2, 3					
0	Off	On					
1	On	Off					

Notes

- QFN EXPOSED PAD TIED TO V-
- N.C. = NO CONNECT
- Switches Shown for Logic "0" Input



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DEVICE OPTIONS										
PART NUMBER	CONFIGURATION	SWITCH FUNCTION	TEMPERATURE RANGE	PACKAGE						
DG1411EN-T1-GE4	Quad SPST	NC	-40 °C to +125 °C	QFN (4 mm x 4 mm) 16L (Variation 2)						
DG1412EN-T1-GE4	Quad SPST	NO	-40 °C to +125 °C	QFN (4 mm x 4 mm) 16L (Variation 2)						
DG1413EN-T1-GE4	Quad SPST	NC/NO	-40 °C to +125 °C	QFN (4 mm x 4 mm) 16L (Variation 2)						
DG1411EQ-T1-GE3	Quad SPST	NC	-40 °C to +125 °C	TSSOP-16						
DG1412EQ-T1-GE3	Quad SPST	NO	-40 °C to +125 °C	TSSOP-16						
DG1413EQ-T1-GE3	Quad SPST	NC/NO	-40 °C to +125 °C	TSSOP-16						

ABSOLUTE MAXIMUM RATIN	GS			
ELECTRICAL PARAMETER	CONDITIONS	LIMITS	UNIT	
V+	Reference to GND	-0.3 V to +25 V		
V-	Reference to GND	+0.3 V to -25 V		
V+ to V-		+35	V	
Analog Inputs (S or D)		V- (-0.3 V) to V+ (+0.3 V)		
Digital Inputs		GND (-0.3 V) to V+ (+0.3 V)		
	TSSOP-16, T _A = 25 °C	190		
Maximum Continuous Switch Current	QFN (4 mm x 4 mm) 16L, T _A = 25 °C	250		
Maximum Continuous Switch Current	TSSOP-16, T _A = 125 °C	90	mA	
	QFN (4 mm x 4 mm) 16L, T _A = 125 °C	100		
Maximum Pulse Switch Current	Pulse at 1 mS, 10 % duty cycle	500		
Thermal Resistance	TSSOP-16	130	°C ///	
mermai Resistance	QFN (4 mm x 4 mm) 16L	32	°C/W	
Temperature				
Operating Temperature		-40 to 125		
Max. Operating Junction Temperature		150	°C	
Operating Junction Temperature		125		
Storage Temperature		-65 to 150		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE							
ELECTRICAL	MINIMUM	MAXIMUM	UNIT				
IN	± 4.5	± 16.5	V				



	l	TEST CONDITIONS			l	1	
PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED V+ = 15 V, V- = -15 V	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	TYP./MAX.	UNIT
		$V_{INH} = 2 V, V_{INL} = 0.8 V$					
Analog Switch							
Analog Signal Range	V _{ANALOG}			V- to V+		-	V
Drain-Source		$V_S = \pm 10 \text{ V}, I_S = -10 \text{ mA}; \text{ see fig. 23}$	1.5	-	-	Тур.	
On-Resistance	R _{DS(on)}	V+ = +13.5 V, V- = -13.5 V	1.8	2.3	2.6	Max.	Ω
ON Desistante Flatures	Б	V . 10 V I 10 1	0.3	-	-	-	
ON-Resistance Flatness	R _{flat(on)}	$V_S = \pm 10 \text{ V}, I_S = -10 \text{ mA}$	0.36	0.45	0.48	Max.	
ON Desistance Matakina	* D		0.08	-	-	Тур.	Ω
ON-Resistance Matching	$\Delta R_{DS(on)}$		0.18	0.19	0.21	Max.	
0. 31-1-0.00110.0011	1 //	V+ = +16.5 V, V- = -16.5 V	± 0.03	-	-	Тур.	
Switch Off Leakage Current	$I_{S}/I_{d(off)}$	$V_S = \pm 10 \text{ V}, V_D = \pm 10 \text{ V}; \text{ see fig. 24}$	± 0.55	± 2	± 12.5	Max.	1 .
		V V 40V 5 05	± 0.15	-	-	Тур.	nA
Channel On Leakage Current	I _{d(on)}	$V_S = V_D = \pm 10 \text{ V}$; see fig. 25	± 2	± 4	± 35	Max.	
Digital Control	L		L		L	•	
Input, High Voltage	V _{INH}		-	-	2	V _{min.}	١ ,,
Input, Low Voltage	V _{INL}		-	-	0.8	V _{max} .	V
			0.005	-	-	Тур.	_
Input Leakage	I _{IN}	$V_{IN} = V_{GND}$ or V+	-	-	± 0.1	Max.	μA
Digital Input Capacitance	C _{IN}		3.5	-	-	Тур.	pF
Dynamic Characteristics			<u>l</u>			71	'
		V _{S1} = V _{S2} = 10 V, see fig. 31;	36	-	-	Typ.	
Break-Before-Make Time	t _{OPEN}	$R_L = 300 \Omega$, $C_L = 35 pF$	-	-	10	Min.	ns
		t_{ON} $V_{S} = 10 \text{ V, see fig. } 30$	100	-	-	Тур.	
Turn-On Time	t _{ON}		150	170	190	Max.	
		$R_L = 300 \Omega$, $C_L = 35 pF$	64	_	-	Typ.	
Turn-Off Time	t _{OFF}		120	140	160	Max.	
Charge Injection	Q _{INj}	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_S = 0 V$ see fig. 32	-20	-	-	Тур.	рС
Off Isolation	OIRR	$C_L = 5 \text{ pF}, R_L = 50 \Omega, 100 \text{ kHz}$	-80	-	-	Тур.	
Cross Talk	X _{TALK}	$C_L = 5 \text{ pF}, R_L = 50 \Omega, 1 \text{ MHz}$	-100	_	_	Тур.	dB
Insertion Loss	TIALK	$f = 1 \text{ MHz}, R_L = 50 \Omega, C_L = 5 \text{ pF}$	-0.08	_		Тур.	-
Total Harmonic Distortion	THD	$R_L = 110 \Omega$, 15 V_{p-p} , $f = 20 \text{ Hz}$ to 20 kHz	0.014	-	-	Тур.	%
Bandwidth, -3dB	BW	$C_L = 5 \text{ pF}, R_L = 50 \Omega$	210	-	-	Тур.	MHz
Source Off Capacitance	C _{S(off)}		11	-	-	Typ.	
Drain Off Capacitance	C _{D(off)}	f = 1 MHz, V _S = 0 V	24	-	-	Тур.	pF
Drain On Capacitance	C _{D(on)}	, 5	87	-	-	Тур.	"
Power Requirements	2(011)						l
Power Supply Range		GND = 0 V		± 4.5/± 1	6.5 min./max	⟨.	V
117 3-		Digital Inputs 0 or V+	0.001	-	-	Тур.	
		V+ = +16.5 V, V- = -16.5 V	-	-	1	Max.	1
	I+		220	_	-	Typ.	
Power Supply Current		IN1 = IN2 = IN3 = IN4 = 5 V	-	_	380	Max.	μA
			0.001	_	-	Typ.	
	I-	Digital Inputs 0 or V+	0.001	I -		ıyρ.	1



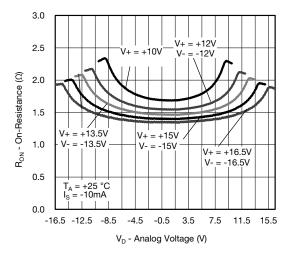
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPI V+ = 12 V, V- = 0 V V _{INH} = 2 V, V _{INL} = 0.8	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	TYP./MAX.	UNIT	
Analog Switch								
Analog Signal Range	V _{ANALOG}				0 V to V+	•		٧
Drain-Source	R _{DS(on)}	$V_S = 0 V \text{ to } 10 V, I_S = -10$		2.8	-	-	Тур.	Ω
On-Resistance	US(on)	see fig. 23, V+ = 10.8 V, V	'- = 0 V	3.5	4.3	4.8	Max.	32
ON-Resistance Flatness	R _{flat(on)}	$V_S = 0 \text{ V to } 10 \text{ V}, I_S = -1$	0.6	-	-	Тур.		
OTT Flooidtaffoo Flatificoo	· mat(on)	V5 = 0 V to 10 V, 15 = 1		1.1	1.2	1.3	Max.	Ω
ON-Resistance Matching	ΔR_{on}			0.08	-	-	Тур.	32
Olf Hediotarioe Matering	Δi ion			0.21	0.23	0.25	Max.	
0. 31-16. 0 (1)1 01	1 /1	V+ = 10.8 V, V- = 0		± 0.02	-	-	Тур.	
Switch Off Leakage Current	I _S /I _{d(off)}	$V_S = 1 \text{ V/10 V, } V_D = 10 \text{ V}$ see fig. 24	V/U V	± 0.55	± 2	± 12.5	Max.	nA
Channel On Leakage Current	1	$V_S = V_D = 1 \text{ V/10 V}$; see f	ia 25	± 0.15	1	-	Тур.	
Chamilei On Leakage Current	I _{d(on)}	v _S = v _D = 1 v/10 v, see 1	ig. 23	± 1.5	± 4	± 30	Max.	
Digital Control								
Input, High Voltage	V _{INH}			-	-	2	Min.	V
Input, Low Voltage	V_{INL}			-	-	0.8	Max.	V
Input Leakage	I _{IN}	$V_{IN} = V_{GND}$ or V+		0.001	i	-	Тур.	μΑ
input Leakage	'IN	VIN - VGND OI V+		-	-	± 0.1	Max.	μΛ
Digital Input Capacitance	C _{IN}			3.5	-	-	Тур.	pF
Dynamic Characteristics								
Break-Before-Make Time	t _{OPEN}	$V_{S1} = V_{S2} = 8 \text{ V}; \text{ see fig. 31},$			-	-	Тур.	
Broak Boloro Mako Timo	OPEN	$R_L = 300 \Omega, C_L = 35 \mu$	ρF	-	-	40	Min.	
Turn-On Time	t _{ON}			210	-	-	Тур.	ns
Tam on time	чОN	$V_S = 8 \text{ V}$; see fig. 30		250	320	360	Max.	110
Turn-Off Time	t _{OFF}	$R_L = 300 \Omega, C_L = 35 \mu$	80	-	-	Тур.		
Tuni on time	OFF			135	165	190	Max.	
Charge Injection	Q_{INj}	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_{S}$ see fig. 32	_S = 6 V	14	-	-	Тур.	рC
Off Isolation	OIRR	D 50 O. C 5 pE	100 kHz	-80	-	-	Тур.	
Cross Talk	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$	1 MHz	-100	-	-	Тур.	dB
Insertion Loss		$f = 1 \text{ MHz}, R_L = 50 \Omega, C_L$	= 5 pF	-0.16	-	-	Тур.	
Bandwidth, -3dB	BW	$R_L = 50 \Omega$, $C_L = 5 pl$	F	200	-	-	Тур.	MHz
Source Off Capacitance	C _{S(off)}			17	-	-	Тур.	
Drain Off Capacitance	C _{D(off)}	$f = 1 MHz, V_S = 6 V$,	30	-	-	Тур.	рF
Drain On Capacitance	C _{D(on)}		94	-	-	Тур.		
Power Requirements								
Power Supply Range		GND = 0 V, V- = 0 \	/		± 5/± 16	3.5 min./max		V
		Digital Inputs 0 or V	+	0.001	-	-	Тур.	
Power Supply Current	1.	V+ = 13.2 V		-	-	1	Max.	
Power Supply Current	l+	IN1 = IN2 = IN3 = IN4 =	- 5 V	220	-	-	Тур.	μA
		11N1 = 11N2 = 11N3 = 11N4 =	-	_	380	Max.		



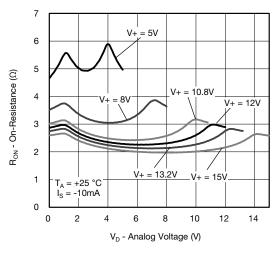
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 5 V, V- = -5 V V _{INH} = 2 V, V _{INL} = 0.8 V	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	TYP./MAX.	UNIT	
Analog Switch				•				
Analog Signal Range	V _{ANALOG}			0 to V+			V	
Drain-Source		$V_S = \pm 4.5 \text{ V}, I_S = -10 \text{ mA}; \text{ see fig. 23},$	3.3	-	-	Тур.		
On-Resistance	R _{DS(on)}	V+ = +4.5 V, V- = -4.5 V	4	4.9	5.4	Max.	Ì	
ON-Resistance Flatness	В	$V_S = \pm 4.5 \text{ V}, I_S = -10 \text{ mA}$	0.9	-	-	Тур.	Ω	
ON-Nesistance Flatness	R _{flat(on)}	V _S = ± 4.5 V, I _S = -10 IIIA	1.1	1.24	1.31	Max.	52	
ON-Resistance Matching	ΔR_{on}		0.08	-	-	Тур.	1	
ON-Nesistance Matching	Δhon		0.22	0.23	0.25	Max.	Ī	
0.11.1.0%110		V+ = +5.5 V, V-= -5.5 V,	± 0.03	-	-	Тур.	1	
Switch Off Leakage Current	I _S /I _{d(off)}	$V_S = +/- 4.5 \text{ V}, V_D = -/+ 4.5 \text{ V};$ see fig. 24	± 0.55	± 2	± 12.5	Max.	nA	
Channel On Leakage Comment	,	$VS = VD = \pm 4.5 V$; see fig. 25	± 0.05	-	-	Тур.		
Channel On Leakage Current	I _{d(on)}	$VS = VD = \pm 4.5 \text{ V, See lig. 25}$	± 1	± 4	± 30	Max.	1	
Digital Control								
Input, High Voltage	V_{INH}		-	-	2	Min.	V	
Input, Low Voltage	V_{INL}		-	-	0.8	Max.	<u> </u>	
Input Leakage	la.	$V_{IN} = V_{GND}$ or V+	0.001	-	-	Тур.	μA	
прит сеакаде	I _{IN}	VIN = VGND OI V+	-	-	± 0.1	Max.	μ, τ	
Digital Input Capacitance	C _{IN}		3.5	-	-	Тур.	рF	
Dynamic Characteristics								
Break-Before-Make Time	topen	$V_{S1} = V_{S2} = 3 \text{ V}$; see fig. 31,		-	-	Тур.	_	
Broak Bororo Wake Time	OPEN	$R_L = 300 \Omega, C_L = 35 pF$	-	-	50	Min.		
Turn-On Time	t _{ON}		300	-	-	Тур.	ns	
Turr on time	UN	$V_S = 3 V$; see fig. 30,	400	465	510	Max.	110	
Turn-Off Time	t _{OFF}	$R_L = 300 \Omega, C_L = 35 pF$	150	-	-	Тур.	1	
Tuni on time	OFF		290	320	380	Max.	<u> </u>	
Charge Injection	Q_{INj}	C_L = 1 nF, R_{GEN} = 0 Ω , V_S = 0 V; see fig. 32	22	-	-	Тур.	рС	
Off Isolation	OIRR	D 50 0 5 75 100 KHz	-80	-	-	Тур.	1	
Cross Talk	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$	-100	-	-	Тур.	dB	
Insertion Loss		$f = 1$ MHz, $R_L = 50$ Ω, $C_L = 5$ pF	-0.19	-	-	Тур.	1	
Bandwidth, -3dB	BW	$R_L = 50 \Omega$, $C_L = 5 pF$	200	-	-	Тур.	MHz	
Source Off Capacitance	C _{S(off)}		18	-	-	Тур.		
Drain Off Capacitance	C _{D(off)}	$f = 1 MHz, V_S = 0 V$	31	-	-	Тур.	pF	
Drain On Capacitance	C _{D(on)}			-	-	Тур.	<u></u>	
Power Requirements								
Power Supply Range		GND = 0 V		± 4.5 V/±	16.5 min./ma	ax.	V	
	l+	Digital Inputs 0 V or V+	0.001	-	-	Тур.	· · · · · · · · · · · · · · · · · · ·	
Power Supply Current	1+	V+ = +5.5 V, V- = -5.5 V	-	-	1	Max.	μ.Λ	
i ower Supply Current	le	Digital Inputs = 0 V or V+	0.001	-	-	Тур.	μΑ	
	I- Digital Inputs = 0 V or V+		_	-	1	Max.		



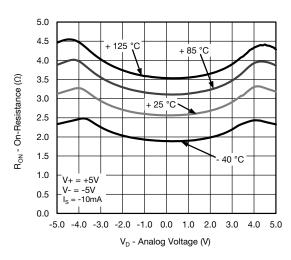
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



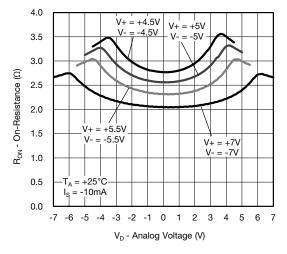
On-Resistance vs. Analog Voltage (DS1)



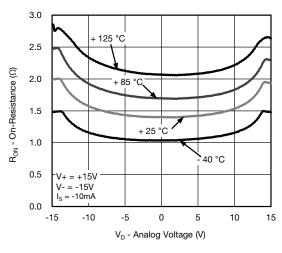
On-Resistance vs. Analog Voltage (DSS)



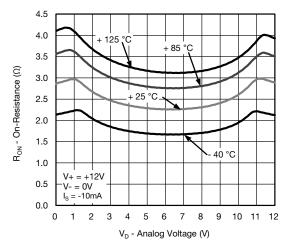
On-Resistance vs. Temperature (± 5 V)



On-Resistance vs. Analog Voltage (DS2)

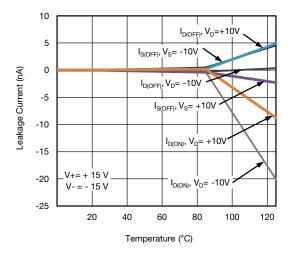


On-Resistance vs. Temperature (± 15 V)

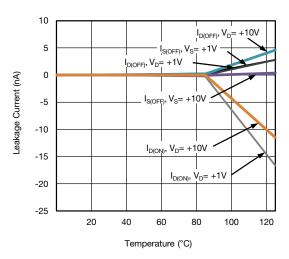


On-Resistance vs. Temperature (+12 V)

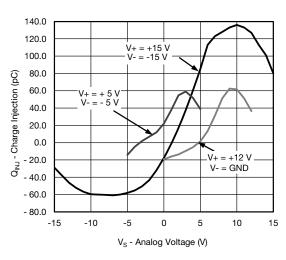
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



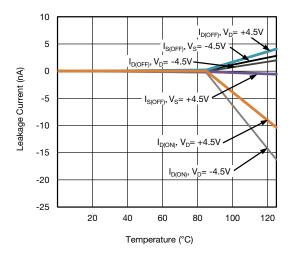
Leakage Current vs. Temperature (± 15 V)



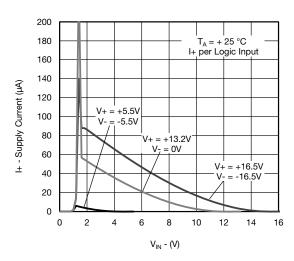
Leakage Current vs. Temperature (+12 V)



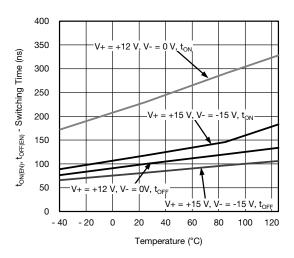
Charge Injection vs. Analog Voltage



Leakage Current vs. Temperature (± 5 V)



Supply Current vs. Logic Level

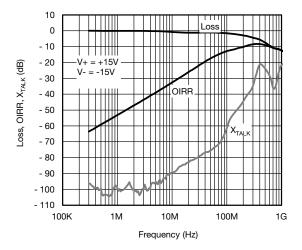


Switching Time vs. Temperature

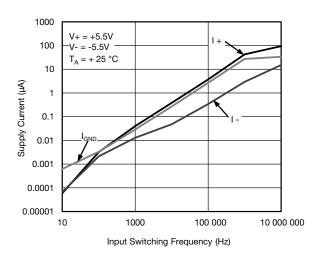
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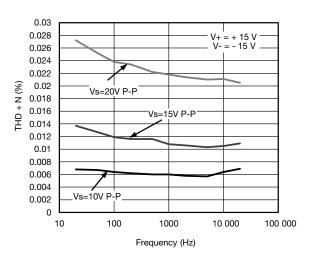
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



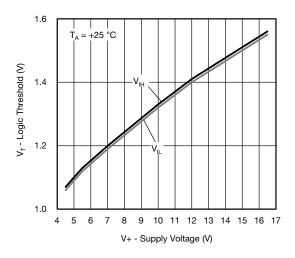
BW, OIRR, X_{TALK} vs. Frequency



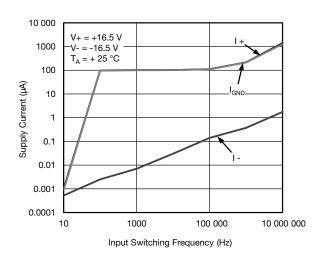
Supply Current vs. Switching Frequency (± 5.5 V)



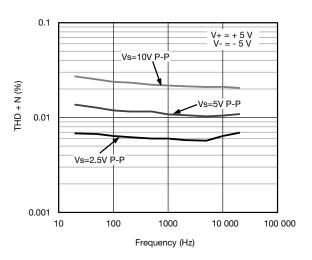
THD vs. Frequency (± 15 V)



Logic Threshold vs. Supply Voltage

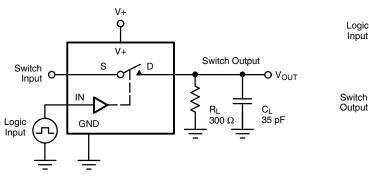


Supply Current vs. Switching Frequency (± 16.5 V)



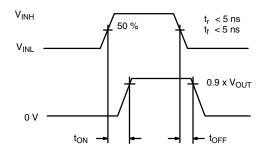
THD vs. Frequency (± 5 V)

TEST CIRCUITS



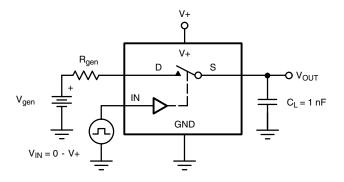
C_L (includes fixture and stray capacitance)

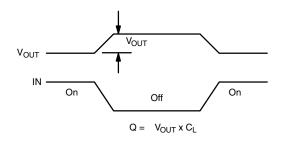
$$V_{OUT} = V_{D} \left(\frac{R_{L}}{R_{L} + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

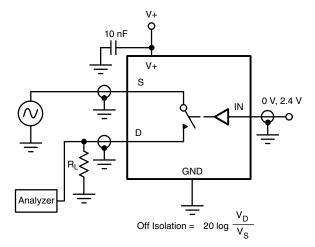
Fig. 1 - Switching Time





IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 2 - Charge Injection





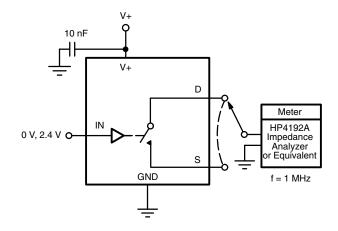
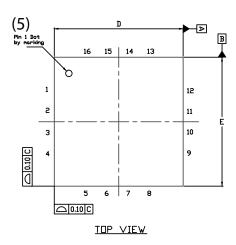


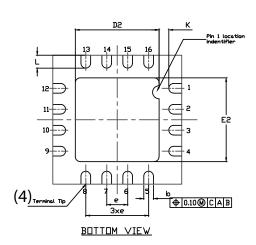
Fig. 4 - Channel Off/On Capacitance

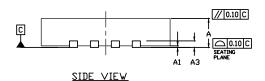
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QFN 4x4-16L Case Outline







	VARIATION 1					VARIATION 1						VARIA	ATION 2		
DIM	МІ	MILLIMETERS(1)		INCHES		MILLIMETERS ⁽¹⁾		S ⁽¹⁾		INCHES					
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.			
Α	0.75	0.85	0.95	0.029	0.033	0.037	0.75	0.85	0.95	0.029	0.033	0.037			
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002			
A3		0.20 ref.			0.008 ref.		0.20 ref.			0.008 ref.					
b	0.25	0.30	0.35	0.010	0.012	0.014	0.25	0.30	0.35	0.010	0.012	0.014			
D		4.00 BSC		0.157 BSC			4.00 BSC			0.157 BSC					
D2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106			
е		0.65 BS0			0.026 BSC		0.026 BSC 0.65 BSC				0.026 BSC				
Е	4.00 BS		4.00 BSC		0.157 BSC			4.00 BSC			0.157 BSC				
E2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106			
K		0.20 min.			0.008 min.			0.20 min.			0.008 min.				
L	0.5	0.6	0.7	0.020	0.024	0.028	0.3	0.4	0.5	0.012	0.016	0.020			
N ⁽³⁾		16 16		16 16		16 16		16			16				
Nd ⁽³⁾	4				4		4			4					
Ne ⁽³⁾		4			4 4				4						

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

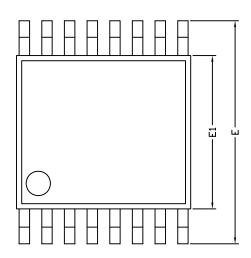
ECN: S13-0893-Rev. B, 22-Apr-13

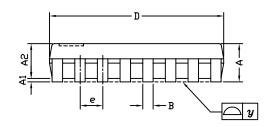
DWG: 5890

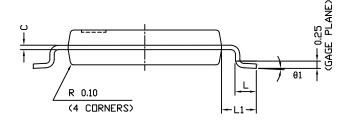
Revision: 22-Apr-13



TSSOP: 16-LEAD







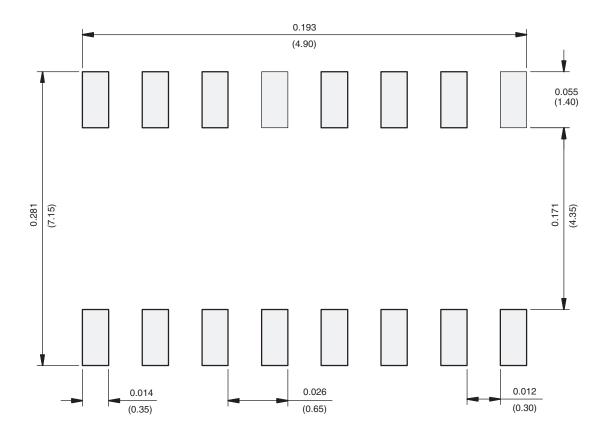
Symbols	DIMENSIONS IN MILLIMETERS		
	Min	Nom	Max
А	=	1.10	1.20
A1	0.05	0.10	0.15
A2	=	1.00	1.05
В	0.22	0.28	0.38
С	=	0.127	-
D	4.90	5.00	5.10
E	6.10	6.40	6.70
E1	4.30	4.40	4.50
е	-	0.65	-
L	0.50	0.60	0.70
L1	0.90	1.00	1.10
у	=	-	0.10
θ1	0°	3°	6°
ECN: S-61920-Rev. D. 23-0	Oct-06	<u> </u>	

DWG: 5624

Document Number: 74417 www.vishay.com 23-Oct-06



RECOMMENDED MINIMUM PAD FOR TSSOP-16



Recommended Minimum Pads Dimensions in inches (mm)



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Revision: 02-Oct-12 Document Number: 91000

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